

GaNpowIR™

High Frequency GaN-Based Integrated Power Stage

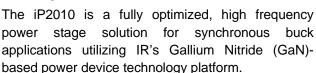
Features

- Input voltage range of 7V to 13.2V
- Output voltage range of 0.6V to 5.5V
- Output current up to 30A
- Benchmark peak and full load efficiency no heat sink required
- Operation up to 3MHz
- Ultrafast, PowlRtune[™] gate driver
- Wireless, low noise flip-chip design
- Industry-standard TTL compatible Enable and PWM inputs
- Small footprint LGA package (7.7mm x 6.5mm x 1.7mm)
- Pin compatible with iP2011

Applications

- Server, Storage and Netcom POL
- General DC/DC Converters





The iP2010 integrates a highly sophisticated, ultra fast PowlRtune driver IC matched to a multi-switch monolithic GaN-based power device. These devices are mounted in a completely wireless package platform to deliver higher efficiency and more than double the switching frequency of state-of-the-art silicon-based integrated power stage devices.

With a switching capability up to 3MHz, the iP2010 enables designers to dramatically reduce the value and size of output capacitors and inductors where space is at premium. The device can also be configured to operate at a lower switching frequency for applications that require the highest possible efficiencies.

Typical Application

